



0015.0010

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: FURUHATA

Serial No.: 09/459,305

Filed: December 10, 1999

For: SEMICONDUCTOR DEVICES, METHODS OF  
MANUFACTURING SEMICONDUCTOR  
DEVICES, CIRCUIT SUBSTRATES AND  
ELECTRONIC DEVICES

Group Art Unit: 2811

Examiner: Tran, T.

#14/B  
F. Bell.  
4.16.02AMENDMENTAssistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sirs:

In response to the Office Action dated September 25, 2001, the time for response being extended to March 25, 2002 by the enclosed petition for extension of time, please enter and consider the following:

## IN THE CLAIMS:

Please cancel claims 1-12 and 20-25 without prejudice.

Please amend claim 13 without prejudice, as follows:

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C1  
B.J.

13. (amended) A semiconductor device comprising:  
tunnel insulating films, floating gates, dielectric films and control gates, all of which are laminated on first and second cell areas on a semiconductor substrate;  
sources and drains formed on the first and second cell areas at positions in contact with a common plane defined by a surface of the semiconductor substrate;  
a connecting area capable of electrically connecting one of the source and drain of the first cell area with one of the source and drain of the second cell area, wherein the connecting area has an electric resistance which is lower than any one of the sources and drains of the first and second cell areas.